

Wonsik Choi

List of Publications by Year in descending order

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12
papers

209
citations

1307594

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1372567

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all docs

12
docs citations

12
times ranked

357
citing authors

#	ARTICLE	IF	CITATIONS
1	III-V Junctionless Gate-All-Around Nanowire MOSFETs for High Linearity Low Power Applications. IEEE Electron Device Letters, 2014, 35, 324-326.	3.9	66
2	Site-Controlled VLS Growth of Planar Nanowires: Yield and Mechanism. Nano Letters, 2014, 14, 6836-6841.	9.1	49
3	Direct Electrical Probing of Periodic Modulation of Zinc-Dopant Distributions in Planar Gallium Arsenide Nanowires. ACS Nano, 2017, 11, 1530-1539.	14.6	25
4	InAs Planar Nanowire Gate-All-Around MOSFETs on GaAs Substrates by Selective Lateral Epitaxy. IEEE Electron Device Letters, 2015, 36, 663-665.	3.9	17
5	Hybrid Integration of n-MoS ₂ /p-GaN Diodes by Quasi-van der Waals Epitaxy. ACS Applied Electronic Materials, 2020, 2, 419-425.	4.3	16
6	Nonlocal Time-Resolved Terahertz Spectroscopy in the Near Field. ACS Photonics, 2021, 8, 2904-2911.	6.6	15
7	Direct Observation of Dopants Distribution and Diffusion in GaAs Planar Nanowires with Atom Probe Tomography. ACS Applied Materials & Interfaces, 2016, 8, 26244-26250.	8.0	11
8	InAs nanowire gate-all-around MOSFETs by heterogeneous planar VLS growth. , 2015, , .		3
9	Selective Area Heteroepitaxy of p-i-n Junction GaP Nanopillar Arrays on Si (111) by MOCVD. IEEE Journal of Quantum Electronics, 2022, 58, 1-6.	1.9	3
10	Monolithic lateral p-n junction GaAs nanowire diodes via selective lateral epitaxy. Nanotechnology, 2021, 32, 505203.	2.6	2
11	Large area MoS ₂ /van der Waals epitaxy on III-Ns and the epitaxial formation of a n-MoS ₂ /p-InGaN diode. , 2016, , .		1
12	Elastocapillary Force Induced Alignment of Large Area Planar Nanowires. ACS Applied Materials & Interfaces, 2021, 13, 11177-11184.	8.0	1